



DMN1008UFDF

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
401/	8mΩ @ V <sub>GS</sub> = 4.5V	12.2A
12V	12.5mΩ @ $V_{GS}$ = 2.5V	10.4A

### Description

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

U-DFN2020-6 (Type F)

# Applications

- Battery Management Application
- Power Management Functions
- DC-DC Converters

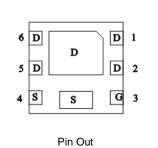
#### 12V N-CHANNEL ENHANCEMENT MODE MOSFET

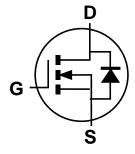
#### Features

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.0065 grams (Approximate)





Bottom View

Internal Schematic

### Ordering Information (Note 4)

Top View

Part Number	Reel Size (inches)	Case	Quantity per Reel
DMN1008UFDF-7	7	U-DFN2020-6 (Type F)	3,000
DMN1008UFDF-13	13	U-DFN2020-6 (Type F)	10,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Bottom View

# Marking Information



8N = Product Type Marking Code YM = Date Code Marking Y = Year (ex: E = 2017)

M = Month (ex: 9 = September)

Date Code Key

Year	2017		2018	2019		2020	2021		2022	2023		2024
Code	E		F	G		Н			J	K		L
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	12	V		
Gate-Source Voltage	V <sub>GSS</sub>	±8	V		
Continuous Drain Current, $V_{GS} = 4.5V$ (Note 6) State $T_A = +25^{\circ}$ $T_A = +70^{\circ}$			ID	12.2 9.8	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%		I <sub>DM</sub>	60	A	
Continuous Source-Drain Diode Current (Note 6)	Is	1.8	А		
Avalanche Current, L = 0.1mH (Note 7)	I <sub>AS</sub>	16.4	A		
Avalanche Energy, L = 0.1mH (Note 7)	E <sub>AS</sub>	13.5	mJ		

### **Thermal Characteristics**

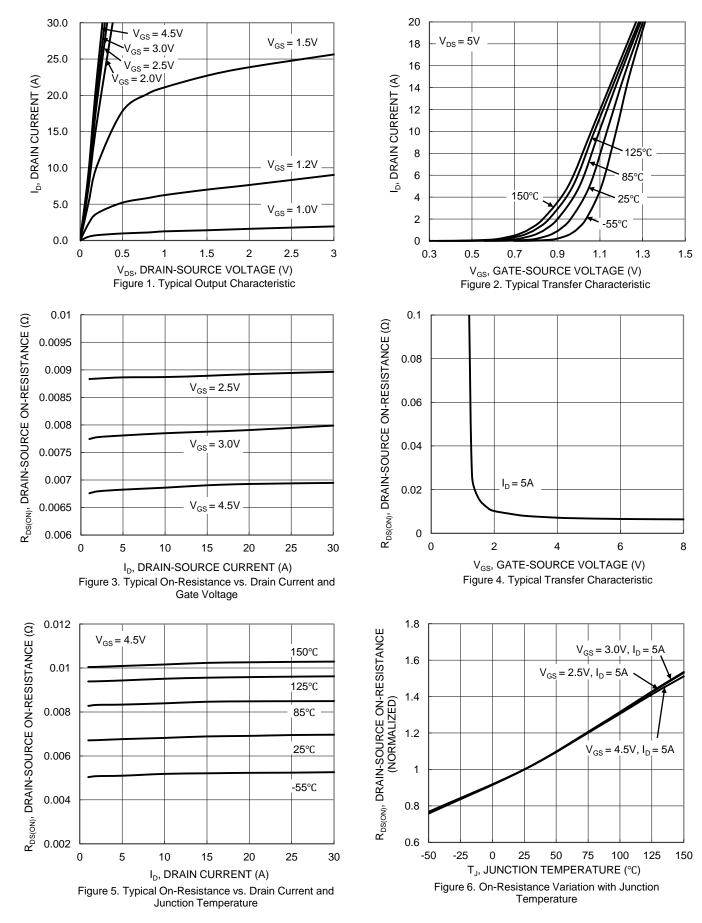
Characteristic		Symbol	Value	Unit
Total Dawar Dissinction (Note 5)	T <sub>A</sub> = +25°C	D	0.7	W
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	PD	0.4	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R <sub>0JA</sub>	168	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	D	1.7	W
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	PD	1.0	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R <sub>0JA</sub>	74	°C/W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	12	°C/W
Operating and Storage Temperature Range		T <sub>J.</sub> T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	<b>•j•</b>		- 71-			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	12	_	—	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current TJ = +25°C	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 9.6V, V <sub>GS</sub> = 0V
Gate-Source Leakage	IGSS	_	—	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)	•					÷
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.3	—	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
			6.6	8		$V_{GS} = 4.5 V, I_D = 5 A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	7.6	11	mΩ	$V_{GS} = 3.0V, I_D = 5A$
			8.5	12.5		$V_{GS} = 2.5V, I_D = 5A$
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 5A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	—	995	-		
Output Capacitance	Coss	—	305	—	pF	$V_{DS} = 6V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	—	270	—		
Gate Resistance	Rg	—	1.5	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	—	13.6	—		
Total Gate Charge (V <sub>GS</sub> = 8V)	Qg	—	23.4	—	nC	
Gate-Source Charge	Qgs	—	1.3	—	nc	$V_{DS} = 6V, I_D = 5A$
Gate-Drain Charge	Q <sub>gd</sub>	—	3.3	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.5	—		
Turn-On Rise Time	t <sub>R</sub>	_	6.6	—		$V_{DS} = 6V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	17.5	—	ns	$R_G = 2\Omega, I_D = 5A$
Turn-Off Fall Time	t <sub>F</sub>	_	7.5	—		
Reverse Recovery Time	t <sub>RR</sub>	_	15	—	ns	I <sub>F</sub> = 5A, di/dt = 200A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	4	—	nC	I <sub>F</sub> = 5A, di/dt = 200A/µs

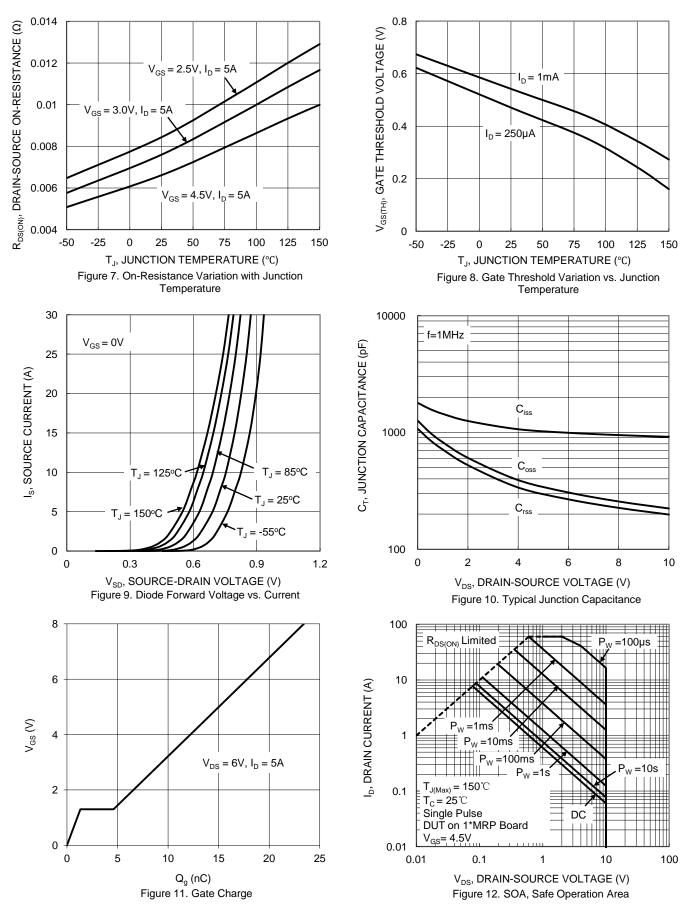
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing. Notes:



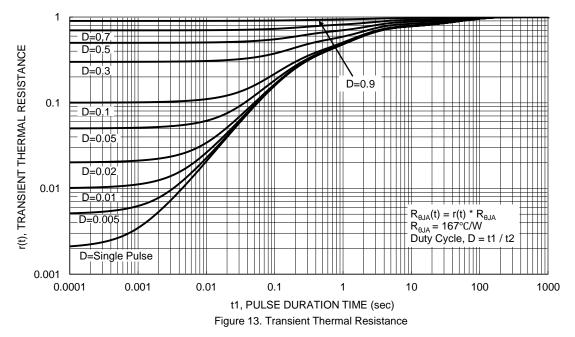




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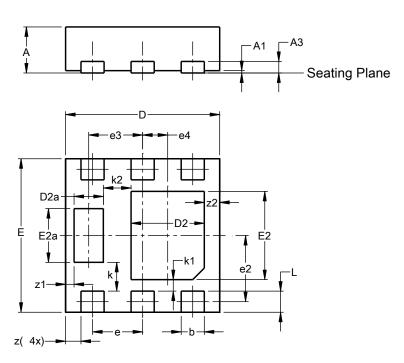






# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

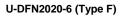


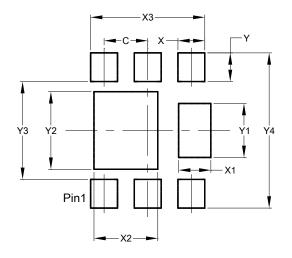
U-DFN2020-6									
	(Type F)								
Dim	Min								
Α	0.57	0.63	0.60						
A1	0.00	0.05	0.03						
A3	-	-	0.15						
b	0.25	0.35	0.30						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
D2a	0.33	0.43	0.38						
E	1.95	2.05	2.00						
E2	1.05	1.25	1.15						
E2a	0.65	0.75	0.70						
е	0.65 BSC								
e2	0.863 BSC								
e3	0.70 BSC								
e4	0.325 BSC								
k	0.37 BSC								
k1	0.15 BSC								
k2	0.36 BSC								
L	0.225 0.325 0.275								
z	0.20 BSC								
z1	0.110 BSC								
z2	0.20 BSC								
All C	All Dimensions in mm								

#### U-DFN2020-6 (Type F)

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.





Dimensions	Value (in mm)		
С	0.650		
Х	0.400		
X1	0.480		
X2	0.950		
X3	1.700		
Y	0.425		
Y1	0.800		
Y2	1.150		
Y3	1.450		
Y4	2.300		



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